

### AS4C64M16D3B-12BCN vs AS4C64M16D3W-12BCN Comparison

Part Number & result Parameter	AS4C64M16D3B-12BCN	AS4C64M16D3W-12BCN	Comparison Result
<b>Product Description</b>	<b>DDR3 SDRAM</b>	<b>DDR3 SDRAM</b>	Same
<b>Die Rev</b>	Rev.B	Rev.W	Different IPs
<b>Capacity</b>	1Gb (64M x 16)	1Gb (64M x 16)	Same
<b>Memory Organization</b>	8M, x16bits, x8 banks	8M, x16bits, x8 banks	Same
<b>Operating Power Supply</b>	$V_{DD} \& V_{DDQ} = 1.5V (\pm 0.075V)$	$V_{DD} \& V_{DDQ} = 1.5V (\pm 0.075V)$	Same
<b>Operating Temperature</b>	Commercial (0°C to 95°C)	Commercial (0°C to 95°C)	Same
<b>Clock Frequency</b>	800MHz	800MHz	Same
<b>Data Rate (MT/s)</b>	1600	1600	Same
<b>CAS Latency</b>	11	11	Same
<b>tRCD &amp; tRP (ns)</b>	13.75	13.75	Same
<b>Average Refresh Period</b>	8192 cycles/64ms	8192 cycles/64ms	Same
<b>I/O Capacitance</b>	CIO: 1.4pf to 2.3pf	CIO: 1.4pf to 2.3pf	Same
<b>Pin to Pin Compatible</b>	Pin to Pin Compatible		Same
<b>AC/DC Characteristics</b>	Same	Same	Meet JEDEC
<b>IDD Specification</b>			
<b>IDD Spec conditions</b>	$0C \leq Tc \leq 95C$ $V_{DD} \& V_{DDQ} = 1.5V (\pm 0.075V)$	$0C \leq Tc \leq 95C$ $V_{DD} \& V_{DDQ} = 1.5V (\pm 0.075V)$	Same
<b>I<sub>DD0</sub> (mA)</b>	56	115	Different
<b>I<sub>DD1</sub> (mA)</b>	72	145	Different
<b>I<sub>DD2P0</sub> (mA)</b>	8	14	Different
<b>I<sub>DD2P1</sub> (mA)</b>	16	40	Different
<b>I<sub>DD2Q</sub> (mA)</b>	35	80	Different
<b>I<sub>DD2N</sub> (mA)</b>	35	80	Different
<b>I<sub>DD3N</sub> (mA)</b>	43	85	Different
<b>I<sub>DD3P</sub> (mA)</b>	28	75	Different
<b>I<sub>DD4R</sub> (mA)</b>	140	280	Different
<b>I<sub>DD4W</sub> (mA)</b>	150	220	Different
<b>I<sub>DD5B</sub> (mA)</b>	95	170	Different
<b>I<sub>DD6</sub> (mA)</b>	8	14	Different
<b>I<sub>DD6ET</sub> (mA)</b>	10	17	Different
<b>I<sub>DD7</sub> (mA)</b>	195	400	Different
<b>I<sub>DD8</sub> (mA)</b>	10	14	Different
<b>Package 96b FBGA</b>	9 x 13 x 1.2mm	9 x 13 x 1.2mm	Same
<b>Package Material</b>	Pb and Halogen Free	Pb and Halogen Free	Same